



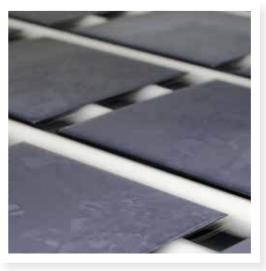


RCT i-Side

RCT i-Side is part of the RCT Inline machine family.

RCT i-Side with its improved process sequence enables high efficiency cell technologies such as PERC, n-type or Bifacial. RCT i-Side polishes wafer with highest reflectivity at cost effective etch depths.

It is optimized for lowest CoO by low chemical consumption, stable processes and small footprint.

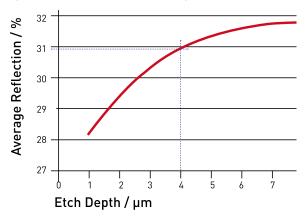


RCT i-Side for single-side junction isolation or polishing

Highlights

- → Improved hydrodynamics of etch bath allows higher reflectivity at lower etch depth, saving 60% of consumables.
- → Patented process sequence with preTreatment, Rinse and junction isolation / polishing.
- → Advanced alkaline cleaning design to avoid KOH contamination.
- → Surface near frequent chemical exchange for high-performance metal impurity cleaning.
- → Unique quick-lock system of spray bars for easy and fast maintenance.
- → Up to 30% reduced DI water consumption due to improved rinse bath perfor mance.

optimum COO at reduced etch depth





textured wafer vs. polished wafer after 4µm etch depth

RCT i-Side Technical Data	
Process	Inline junction isolation / polishing and cleaning
Throughput	3,600 w/h gross, 5 lanes
Conveyor speed	0.5 – 2.5 m/min, nominal 2.1 m/min
Dimensions	8880 x 2200 x 2120 mm³ (L x W x H)
Wafer size	156 x 156 ± 0.5mm / 156.75 × 156.75 ± 0.25mm, ≥ 150 μ m
Etch depth range	0.7 – 6 μm
Bath lifetime	> 1,500,000 wafers
Breakage Rate	< 0.05%

